

Remarks

As indicated above, the present Amendment is being submitted as a supplement to the earlier filed, unentered Amendment After Final, dated June 27, 2003, in keeping with the understanding reached with the Examiner in charge of the above-referenced application during a personal interview with him on July 21, 2003. The earlier filed unentered Amendment After Final as supplemented herein is to be considered as part of the submission in connection with the filing of the accompanying RCE (Request for Continued Examination) transmittal. **It is also respectfully requested that further prosecution with regard to the above-identified application be suspended for a period of three (3) months, as is permitted under 37 CFR §1.103(c).** This request is being made to give applicants the additional time needed to prepare additional supportive material to be submitted, in due course, including but not limited to a declaration.

Turning back to the revisions implemented hereinabove, these changes are being implemented to highlight the fact that the featured aspect directed to the "glass substrate" is defining of the glass substrate in terms of a physical property thereof. This additional revision was discussed during the interview with the Examiner and is being incorporated into each of the independent claims 1 and 9, in keeping with the understanding reached with the Examiner during the above-mentioned interview. The following discussion represents the substance of the interview held on July 21, 2003, in keeping with MPEP §713.04.

Applicants undersigned representative reiterated the points of argument earlier presented in the remarks of the Amendment filed on June 27, 2003. In that regard, particular emphasis was given concerning the structural differences

between that of the "glass substrate" defined in base claims 1 and 9 of the present invention with that taught by Yamazaki et al ('630) and Abe et al (JP 8-195494). It was also agreed, during the interview, that the "glass substrate", as defined in the claims, pertains to the physical properties of the glass substrate itself and does not concern a "product-by-process" limitation. In order to highlight this further and avoid any further concern the Examiner may have had, the expression pertaining to the "glass substrate" in both of those claims is being revised as noted hereinabove. This revision is in keeping with the understanding reached with the Examiner, during the above-held interview, concerning that featured aspect. That is, the above revisions would remove any remaining concern, according to the Examiner, regarding the expression in the claims directed to the "glass substrate." The Examiner indicated, also, that a more favorable consideration would likely be given to the claimed subject matter, assuming that no further relevant art documents are uncovered, if there is submitted, also, a supportive showing (in the form of a Declaration) characterizing the "glass substrate," according to claims 1 and 9, as a structurally different element, namely, whose physical properties are different from that employed by Yamazaki et al ('630) as well as by Abe et al.

As stated in the Examiner's comments of the Interview Summary (form PTO 413), the earlier filed Amendment was discussed. However, the Examiner indicated that the Amendment of June 27, 2003 would not be entered due to the "substantive changes being implemented in base claim 1" which, according to the Examiner, "changes the scope of the dependent claim 22 thereof" as well as with regard to the changes implemented in independent claim 9 which "changes the scope of claims 9 and 11, thereby "requir[ing] further consideration and/or

search," according to the Examiner. He therefore suggested that a RCE be considered. (See the Examiner's added comments in the Interview Summary.) No further substantive discussed was involved at the time of the interview.

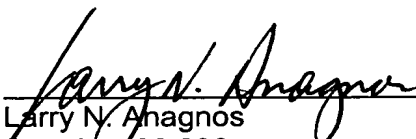
Since the Examiner is refusing to formally enter/consider the responsive Amendment After Final, filed on June 27, 2003, applicants have decided to continue prosecution in connection with the USPTO RCE procedure. In that regard, the earlier filed responsive Amendment After Final as supplemented herein is to be considered as part of the submission pursuant to 37 CFR § 1.114. Acceptance and formal entry therefor of the same is respectfully requested. In the meantime, applicants, through their undersigned representative, have also requested suspension of further prosecution for a period of three (3) months to give them sufficient time to consider further the matter at hand including with regard to any additional responsive arguments to be prepared including the filing of any Declaration directed thereto. Incidentally, the Examiner's courteousness at the time of the interview is greatly appreciated.

A marked-up version showing changes made is enclosed herewith.

To the extent necessary, applicants petition for an extension of time under 37 CFR §1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees to the Deposit Account of

Antonelli, Terry, Stout & Kraus, LLP, Dep. Acct. No. 01-2135 (566.40894X00),
and please credit any excess fees to such deposit account.

Respectfully submitted,
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703-312-6600

MARKED-UP VERSION SHOWING CHANGES MADE

IN THE CLAIMS:

Please **amend** claims 1 and 9 as follows:

1. (Thrice Amended) A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate, a channel region, a source region, a drain region, a first insulating layer and a second insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

said glass substrate is defined as having a physical property such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute,

said first insulating layer covers said channel region and has a layer thickness whose lower limit is 4nm, and

said second insulating layer is formed on a surface of said first insulating layer.

9. (Thrice Amended) A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate, a channel region, a source region, a drain region and an insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

said glass substrate is defined as having a physical property such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute, and

said insulating layer covers said channel region and has a layer thickness defined by the range 4nm to 20nm.